

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

BU2520A

DESCRIPTION

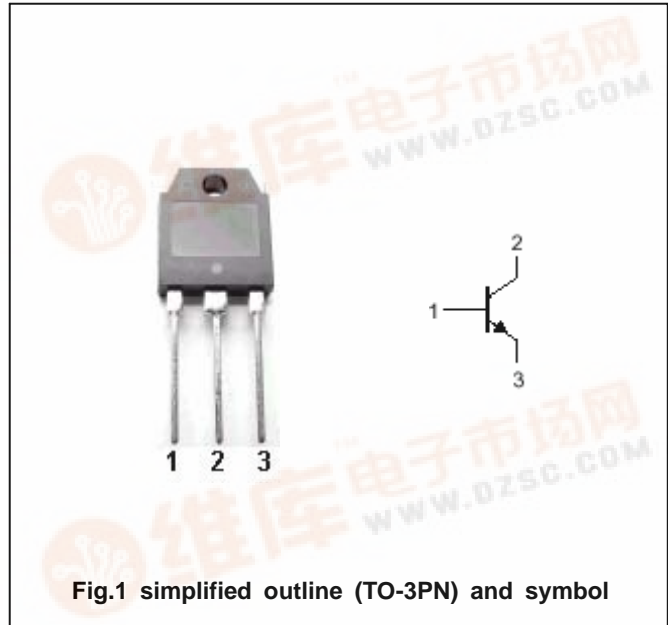
- With TO-3PN package
- High voltage
- High speed switching

APPLICATIONS

- For use in horizontal deflection circuits of large screen colour TV receivers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7.5	V
I_C	Collector current (DC)		10	A
I_{CM}	Collector current (Pulse)		25	A
I_B	Base current		6	A
I_{BM}	Base current(peak)		9	A
P_C	Collector power dissipation	$T_C=25$	125	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter breakdown voltage	I _C =100mA; I _B =0; L=25mH	700			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	7.5	13.5		V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =1.2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =1.2A			1.3	V
I _{CES}	Collector cut-off current	V _{CE} =rated; V _{BE} =0 T=125 ° C			1.0 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7.5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =5V	6	13	26	
h _{FE-2}	DC current gain	I _C =6A ; V _{CE} =5V	5	7	10	
C _C	Collector capacitance	I _E =0 V _{CB} =10V; f=1MHz		115		pF

